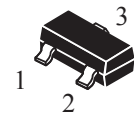


Surface Mount Switching Diode

Features:

- *Low Current Leakage
- *Low Forward Voltage
- *Ultra High Speed Switching
- *Small Outline Surface Mount SOT-23 Package

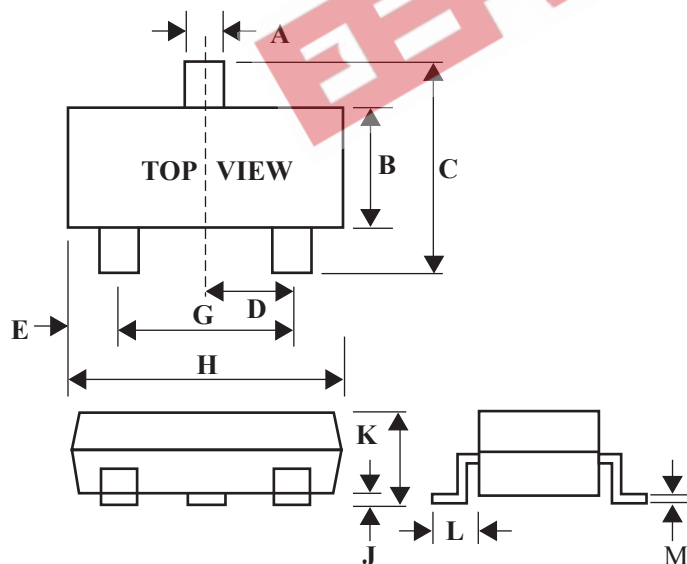
SWITCHING DIODE
100m AMPERRES
80 VOLTS



SOT-23

SOT-23 Outline Dimensions

Unit:mm



Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25

Maximum Ratings (EACH DIODE)

Characteristic	Symbol	WAN202K	WANP202K	WAN217	Unit
Reverse Voltage	V_R	80			Volts
Forward Current	I_F	100			mAdc
Peak Forward Surge Current	I_{FM}	300			mAdc

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board *1, $T_A=25^\circ\text{C}$ Derate Above 25°C	P_D	200 1.6	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to + 150	$^\circ\text{C}$

*1 ER-5=1.0x0.75x0.062 in

Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Note) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage ($I_{BR}=100\mu\text{Adc}$)	V_{BR}	80		Vdc
Reverse Voltage Leakage Current $V_R=70\text{V}$	I_R		0.1	μAdc
Diode Capacitance ($V_R=6\text{Vdc}$, $f=1.0\text{MHz}$)	C_D		3.5	PF
Forward Voltage ($I_F=100\text{mAdc}$)	V_F		1.2	Vdc
Reverse Recovery Time (Figure 1.) $I_R=5.0\text{mAdc}$, $V_R=6.0\text{Vdc}$	t_{rr}		4.0	nS

Device Marking

Item	Marking	Equivalent Circuit diagram
WAN202K	A4	
WAP202K	A1	
WAN217	A7	

Figure 1. Recovery Time Equivalent Test Circuit

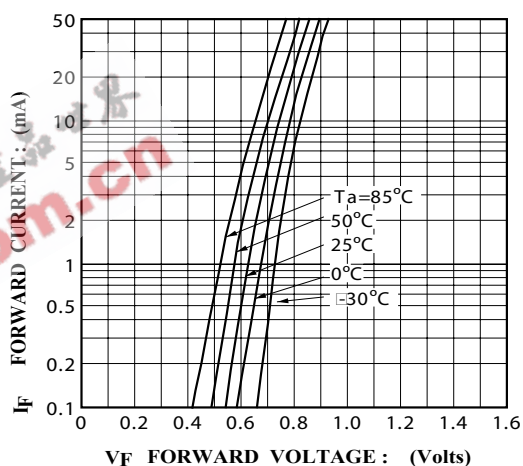
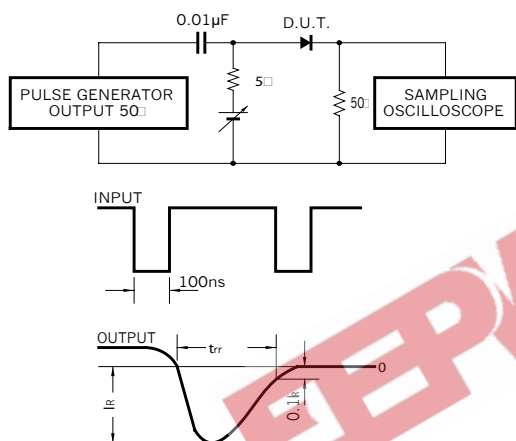


Fig.2 Forward characteristics

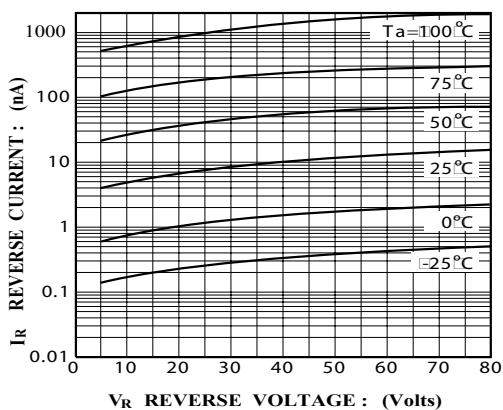


Fig.3 Reverse characteristics

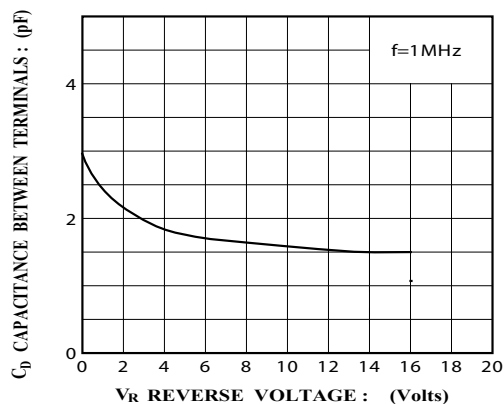


Fig.4 Capacitance